

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC5259

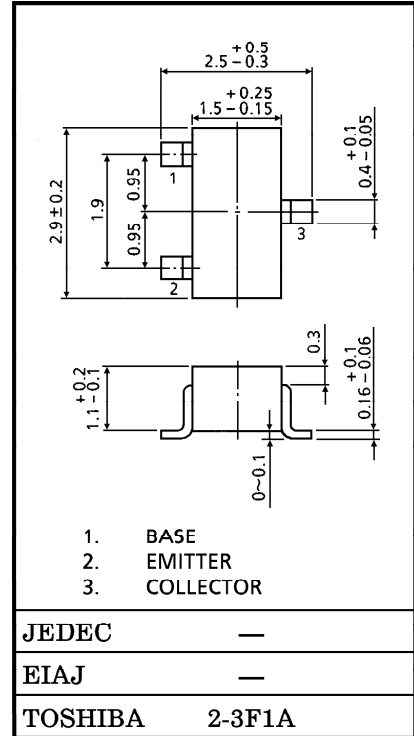
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Unit in mm

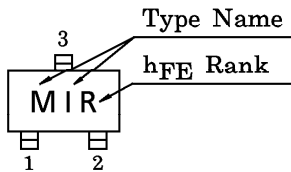
- Low Noise Figure : NF=1.7dB (f=2GHz)
- High Gain : Gain=8.5dB (f=2GHz)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	15	V
Collector-Emitter Voltage	V _{CEO}	7	V
Emitter-Base Voltage	V _{EB0}	1.5	V
Collector Current	I _C	15	mA
Base Current	I _B	7	mA
Collector Power Dissipation	P _C	150	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



MARKING



MICROWAVE CHARACTERISTICS (Ta = 25°C)

Weight : 12mg

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f _T	V _{CE} =5V, I _C =7mA	9	12	—	GHz
Insertion Gain	S _{21e} ² (1)	V _{CE} =5V, I _C =7mA, f=1GHz	11.5	14.5	—	dB
	S _{21e} ² (2)	V _{CE} =5V, I _C =7mA, f=2GHz	5.5	8.5	—	
Noise Figure	NF (1)	V _{CE} =5V, I _C =3mA, f=1GHz	—	1.3	—	dB
	NF (2)	V _{CE} =5V, I _C =3mA, f=2GHz	—	1.7	3	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} =10V, I _E =0	—	—	1	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} =1V, I _C =0	—	—	1	μA
DC Current Gain	h _{FE} (Note 1)	V _{CE} =5V, I _C =7mA	50	—	160	—
Output Capacitance	C _{ob}	V _{CB} =5V, I _E =0, f=1MHz (Note 2)	—	0.4	—	pF
Reverse Transfer Capacitance	C _{re}		—	0.3	0.7	pF

(Note 1) : h_{FE} Classification R : 50~100, O : 80~160

(Note 2) : C_{re} is measured by 3 terminal method with capacitance bridge.

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